

**Leistungsstarke IR-Lumineszenzdiode**  
**High Power Infrared Emitter**  
**Lead (Pb) Free Product - RoHS Compliant**

**SFH 4209**



**Nicht für Neuentwicklungen / Not for new designs**

**Wesentliche Merkmale**

- Leistungsstarke GaAs-LED (40mW)
- Hoher Wirkungsgrad bei kleinen Strömen
- Typische Peakwellenlänge 950nm

**Features**

- High Power GaAs-LED (40mW)
- High Efficiency at low currents
- Typical peak wavelength 950nm

**Anwendungen**

- Schnelle Datenübertragung mit Übertragungsraten bis 100 Mbaud (IR Tastatur, Joystick, Multimedia)
- Analoge und digitale Hi-Fi Audio- und Videosignalübertragung
- Batteriebetriebene Geräte (geringe Stromaufnahme)
- Anwendungen mit hohen Zuverlässigkeitsansprüchen bzw. erhöhten Anforderungen
- Alarm- und Sicherungssysteme
- IR Freiraumübertragung

**Applications**

- High data transmission rate up to 100 Mbaud (IR keyboard, Joystick, Multimedia)
- Analog and digital Hi-Fi audio and video signal transmission
- Low power consumption (battery) equipment
- Suitable for professional and high-reliability applications
- Alarm and safety equipment
- IR free air transmission

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung <sup>1)</sup> ( $I_F = 100\text{mA}$ , $t_p = 20\text{ ms}$ ) Radiant Intensity Grouping <sup>1)</sup> $I_e$ (mW/sr)
SFH 4209	Q65110A2501	24 (> 10)

<sup>1)</sup> gemessen bei einem Raumwinkel  $\Omega = 0.01$  / measured at a solid angle of  $\Omega = 0.01$  sr

Grenzwerte ( $T_A = 25\text{ °C}$ )

## Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	$V_R$	3	V
Durchlaßstrom Forward current	$I_F$ (DC)	100	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$ , $D = 0$ Surge current	$I_{FSM}$	2.2	A
Verlustleistung Power dissipation	$P_{tot}$	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je $16\text{ mm}^2$ Thermal resistance junction - ambient mounted on PC-board (FR4), padsize $16\text{ mm}^2$ each	$R_{thJA}$	450	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	$R_{thJS}$	200	K/W

**Kennwerte** ( $T_A = 25\text{ °C}$ )**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\lambda_{\text{peak}}$	950	nm
Spektrale Bandbreite bei 50% von $I_{\text{max}}$ Spectral bandwidth at 50% of $I_{\text{max}}$ $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\Delta\lambda$	40	nm
Abstrahlwinkel Half angle	$\varphi$	$\pm 25$	Grad deg.
Aktive Chipfläche Active chip area	$A$	0.09	mm <sup>2</sup>
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	$0.3 \times 0.3$	mm <sup>2</sup>
Schaltzeiten, $I_e$ von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ , $R_L = 50\ \Omega$ Switching times, $I_e$ from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ , $R_L = 50\ \Omega$	$t_r$ , $t_f$	10	ns
Durchlassspannung, Forward voltage $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$ , $t_p = 100\ \mu\text{s}$	$V_F$ $V_F$	1.5 ( $\leq 1.8$ ) 3.2 ( $\leq 4.3$ )	V V
Sperrstrom Reverse current $V_R = 3\text{ V}$	$I_R$	0.01 ( $\leq 10$ )	$\mu\text{A}$
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\Phi_e$	40	mW
Temperaturkoeffizient von $I_e$ bzw. $\Phi_e$ , $I_F = 100\text{ mA}$ Temperature coefficient of $I_e$ or $\Phi_e$ , $I_F = 100\text{ mA}$	$TC_I$	- 0.44	%/K
Temperaturkoeffizient von $V_F$ , $I_F = 100\text{ mA}$ Temperature coefficient of $V_F$ , $I_F = 100\text{ mA}$	$TC_V$	- 1.5	mV/K
Temperaturkoeffizient von $\lambda$ , $I_F = 100\text{ mA}$ Temperature coefficient of $\lambda$ , $I_F = 100\text{ mA}$	$TC_\lambda$	+ 0.2	nm/K

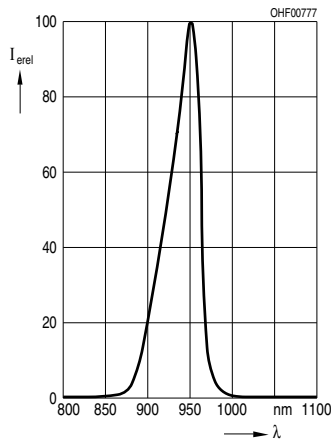
**Strahlstärke  $I_e$  in Achsrichtung<sup>1)</sup>**gemessen bei einem Raumwinkel  $\Omega = 0.01$  sr**Radiant Intensity  $I_e$  in Axial Direction**at a solid angle of  $\Omega = 0.01$  sr

Bezeichnung Parameter	Symbol	Werte Values			Einheit Unit
		SFH 4209-R	SFH 4209-S	SFH 4209-T	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min}}$ $I_{e \text{ max}}$	10 20	16 32	25 50	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ $\mu$ s	$I_{e \text{ typ.}}$	100	140	180	mW/sr

<sup>1)</sup> Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1)<sup>1)</sup> Only one group in one packing unit, (variation lower 2:1)

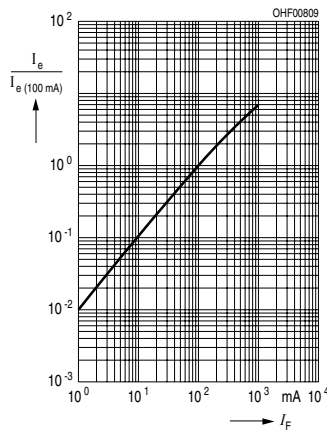
**Relative Spectral Emission**

$I_{rel} = f(\lambda)$



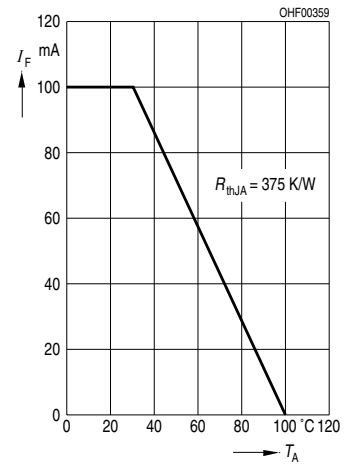
**Radiant Intensity**  $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse,  $t_p = 20 \mu\text{s}$



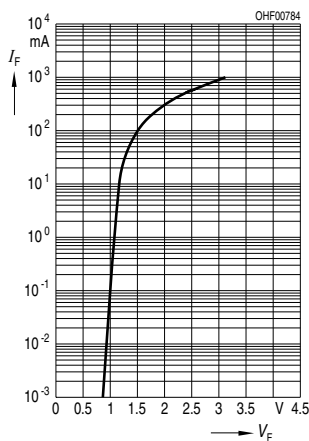
**Max. Permissible Forward Current**

$I_F = f(T_A), R_{thJA}^1$



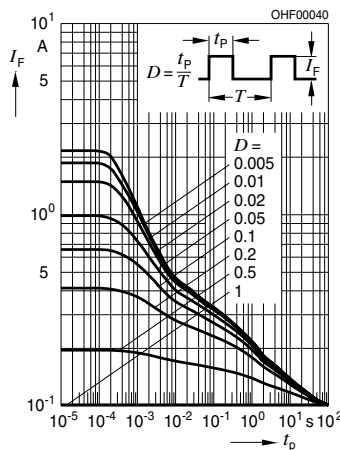
**Forward Current**  $I_F = f(V_F)$

single pulse,  $t_p = 20 \mu\text{s}$

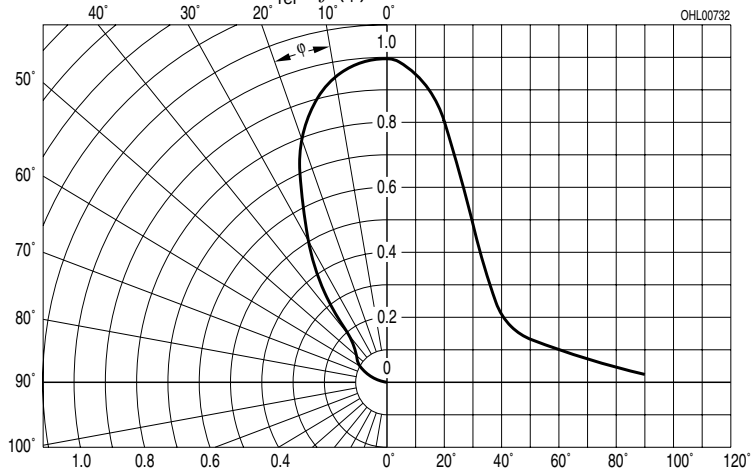


**Permissible Pulse Handling Capability**

$I_F = f(\tau), T_A = 25 \text{ }^\circ\text{C}$ ,  
duty cycle  $D = \text{parameter}$

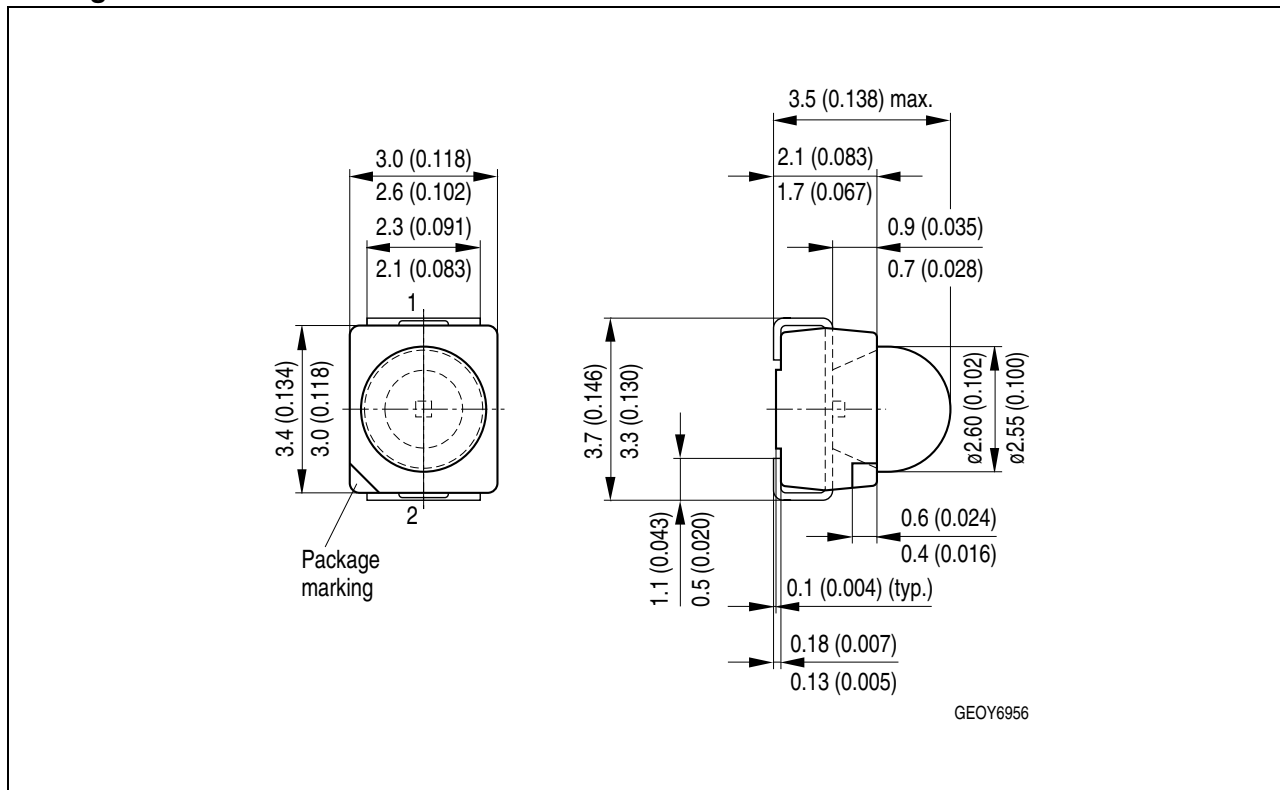


**Radiation Characteristics**  $I_{rel} = f(\varphi)$



<sup>1)</sup> Thermal resistance junction - ambient mounted on PC-board (FR4), pad size 16 mm<sup>2</sup> (each).

## Maßzeichnung Package Outlines

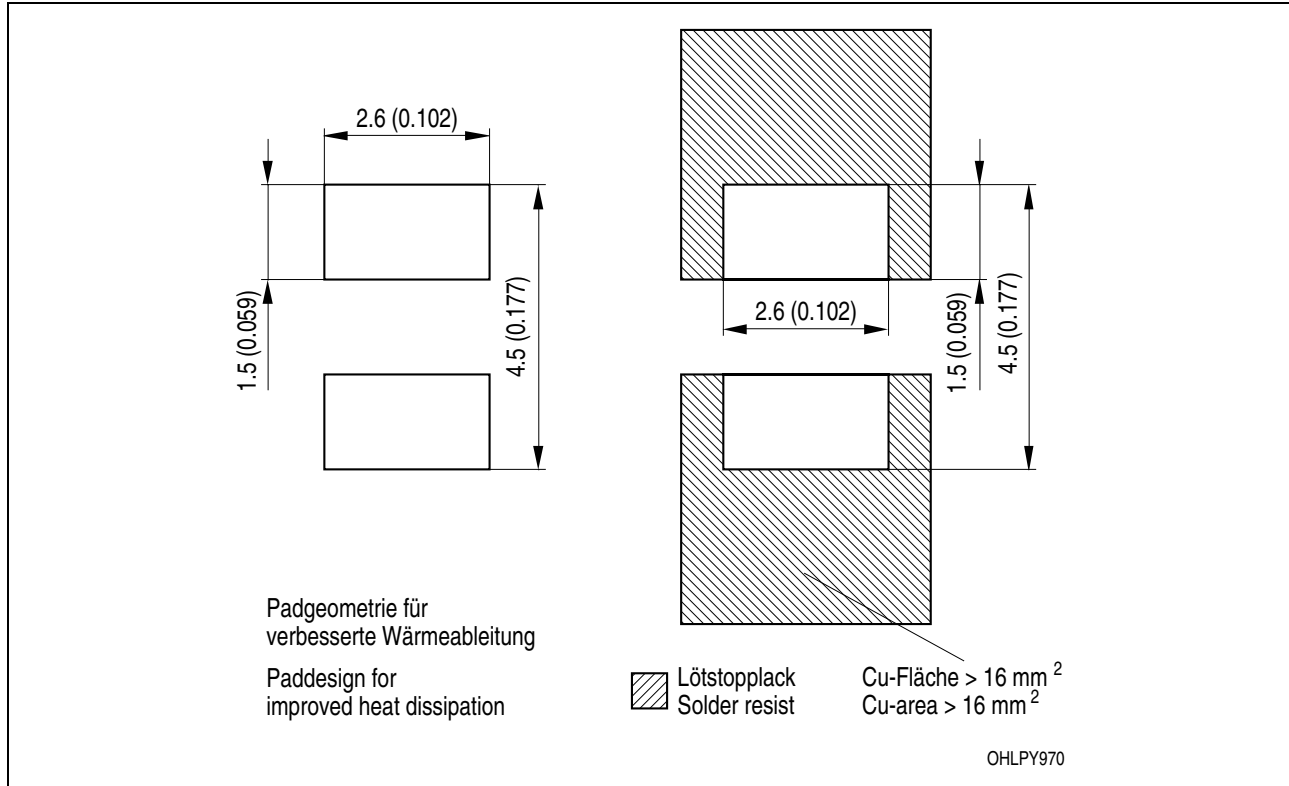


Maße in mm (inch) / Dimensions in mm (inch).

Gehäuse / Package	TOPLED® mit Linse (P-LCC-2) / TOPLED® with lens (P-LCC-2)
Anschlussbelegung pin configuration	1 = Anode / anode 2 = Kathode / cathode
Farbe Color	weiß white

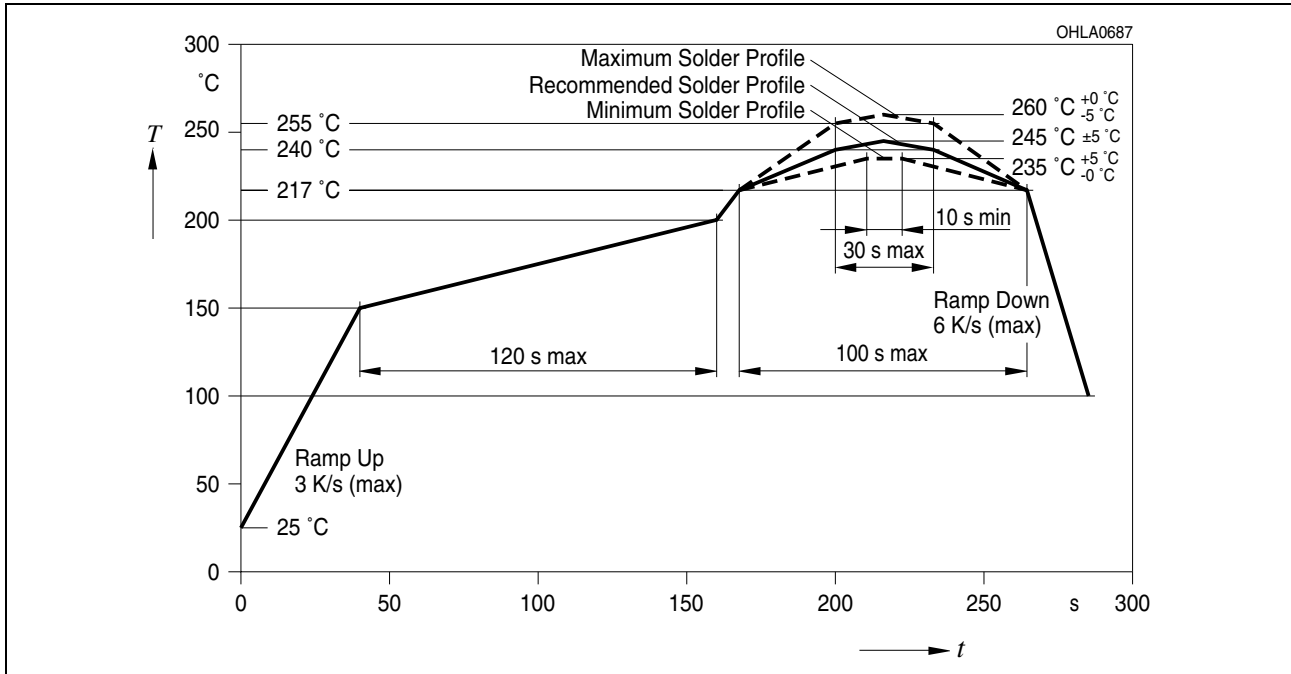
**Empfohlenes Lötpad-Design**  
**Recommended Solder Pad**

**Reflow Löten**  
**Reflow Soldering**



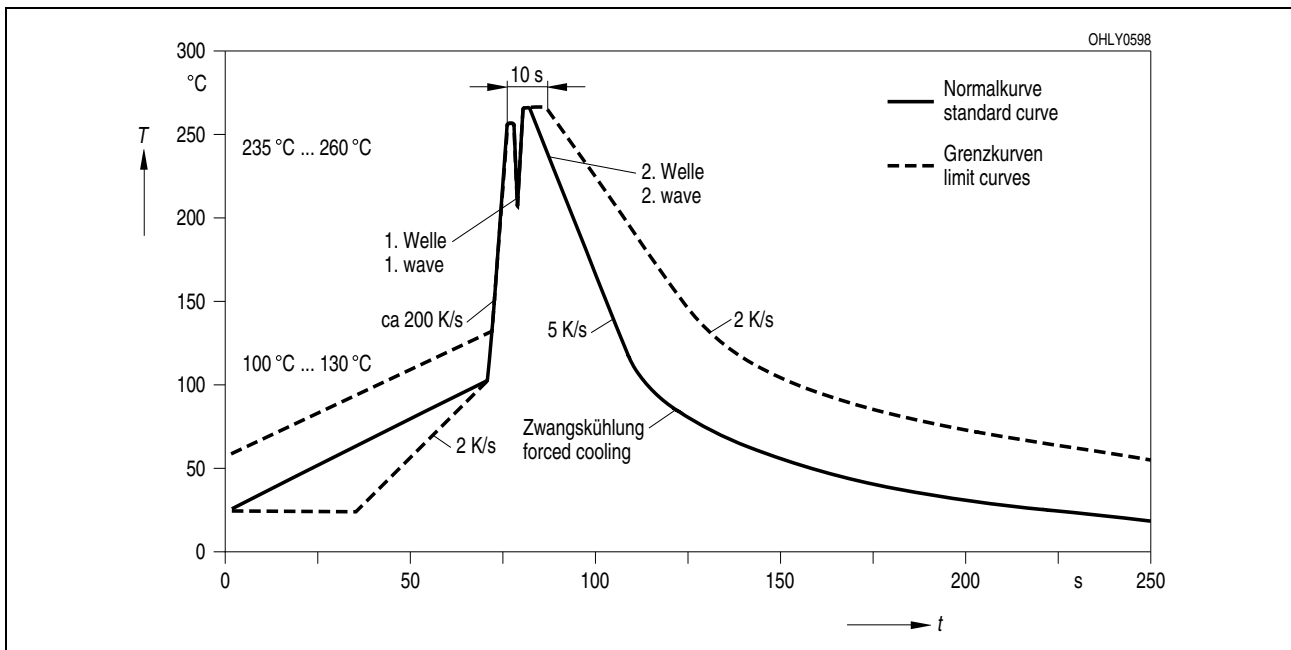
**Lötbedingungen**  
**Soldering Conditions**  
**Reflow Lötprofil für bleifreies Löt**  
**Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 2  
 Preconditioning acc. to JEDEC Level 2  
 (nach J-STD-020C)  
 (acc. to J-STD-020C)



**Wellenlöten (TTW)**  
**TTW Soldering**

(nach CECC 00802)  
 (acc. to CECC 00802)





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<sup>1</sup> A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

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